

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
60V	85mΩ @ V _{GS} = 10V	4.1A
	110mΩ @ V _{GS} = 4.5V	3.6A

Features and Benefits

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](#) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

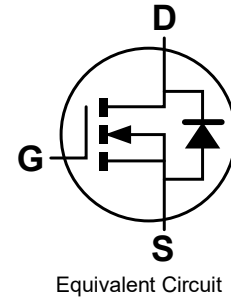
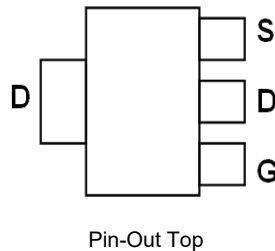
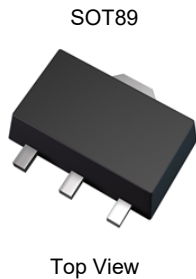
Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- DC-DC converters
- Power-management functions
- Backlighting

Mechanical Data

- Package: SOT89
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Finish Annealed over Copper Lead Frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.052 grams (Approximate)

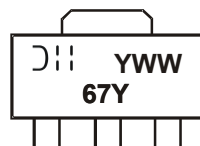


Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMN6070SY-13	SOT89	2,500	Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



- Dii = Manufacturer's Marking
- 67Y = Product Type Marking Code
- YWW = Date Code Marking
- Y or Y̅ = Year (ex: 6 = 2026)
- WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C	I _D	4.1	A
		T _A = +70°C		3.3	
Pulsed Drain Current (10µs Pulse, Duty Cycle ≤ 1%)			I _{DM}	15	A
Maximum Body Diode Continuous Current (Note 6)			I _S	2.5	A
Pulsed Body Diode Current (10µs Pulse, Duty Cycle ≤ 1%)			I _{SM}	15	A
Avalanche Current, L = 0.1mH (Note 7)			I _{AS}	11	A
Avalanche Energy, L = 0.1mH (Note 7)			E _{AS}	6	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	122	°C/W
	t < 10s		72	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	2.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	58	°C/W
	t < 10s		34	°C/W
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	12	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	I _D = 250µA, V _{GS} = 0
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 60V, V _{GS} = 0
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±16V, V _{DS} = 0
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	—	3.0	V	I _D = 250µA, V _{DS} = V _{GS}
Static Drain-Source On-Resistance	R _{DS(ON)}	—	70	85	mΩ	V _{GS} = 10V, I _D = 2.5A
			76	110		V _{GS} = 4.5V, I _D = 1.5A
Diode Forward Voltage	V _{SD}	—	0.75	1.2	V	I _S = 12A, V _{GS} = 0
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	588	—	pF	V _{DS} = 30V, V _{GS} = 0 F = 1MHz
Output Capacitance	C _{oss}	—	26.5	—		
Reverse Transfer Capacitance	C _{rss}	—	20	—		
Gate Resistance	R _g	—	1.5	—	Ω	V _{GS} = 0, V _{DS} = 0, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	5.6	—	nC	V _{DS} = 30V, I _D = 3A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	12.3	—		
Gate-Source Charge	Q _{gs}	—	1.7	—		
Gate-Drain Charge	Q _{gd}	—	1.9	—		
Turn-On Delay Time	t _{D(ON)}	—	3.5	—	ns	V _{DD} = 30V, V _{GS} = 10V R _L ≅ 50Ω, R _g ≅ 20Ω
Turn-On Rise Time	t _R	—	4.1	—		
Turn-Off Delay Time	t _{D(OFF)}	—	35	—		
Turn-Off Fall Time	t _F	—	11	—		
Body Diode Reverse-Recovery Time	t _{RR}	—	18	—	ns	I _S = 12A, di/dt = 100A/µs
Body Diode Reverse-Recovery Charge	Q _{RR}	—	12	—	nC	I _S = 12A, di/dt = 100A/µs

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

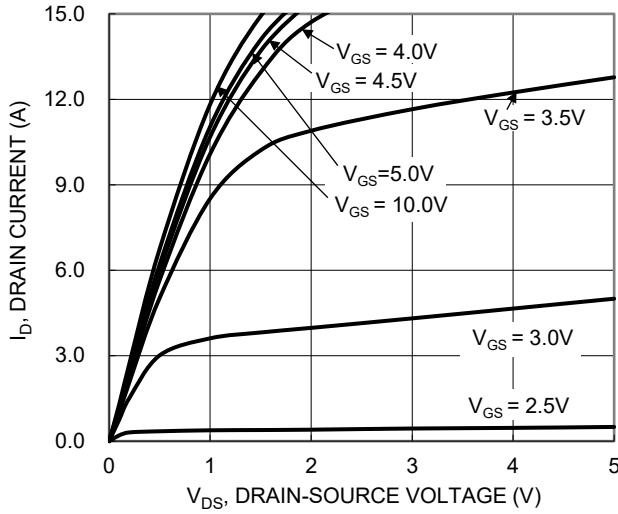


Figure 1. Typical Output Characteristic

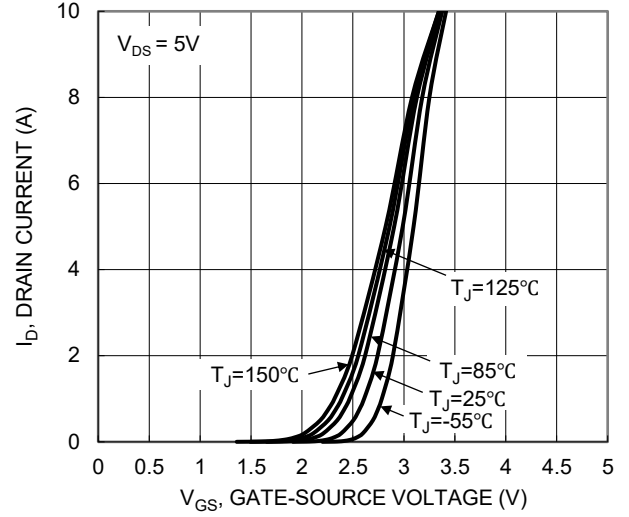


Figure 2. Typical Transfer Characteristic

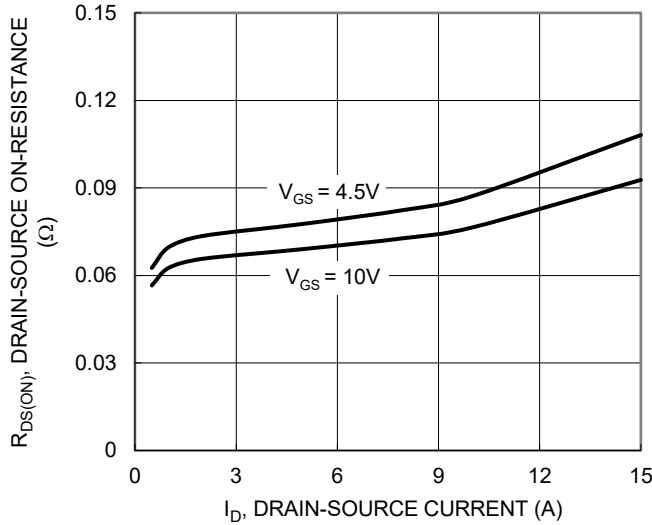


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

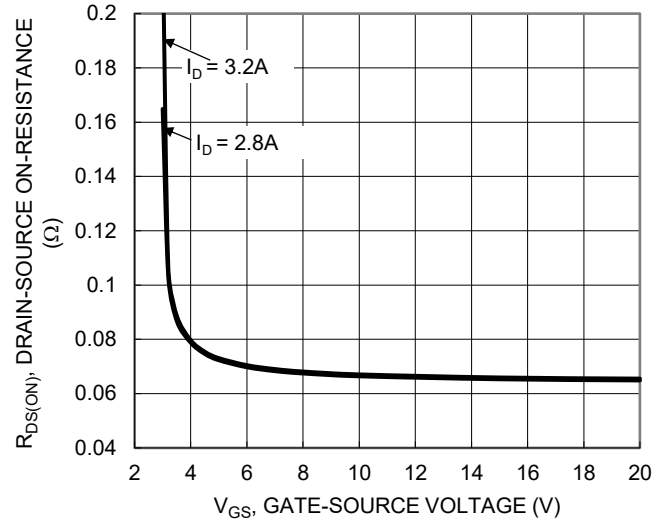


Figure 4. Typical Transfer Characteristic

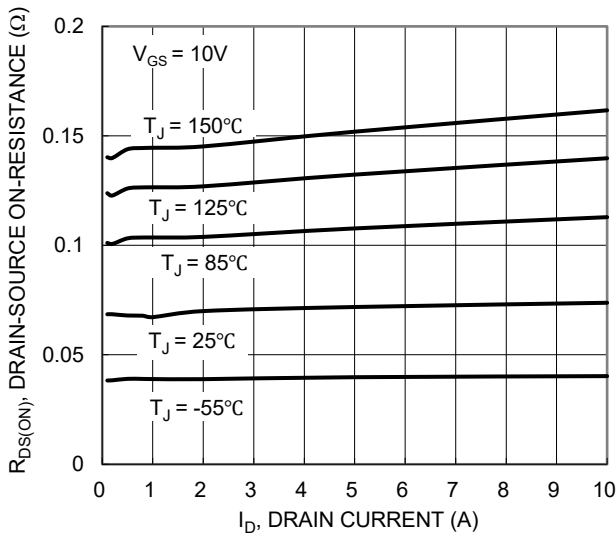


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

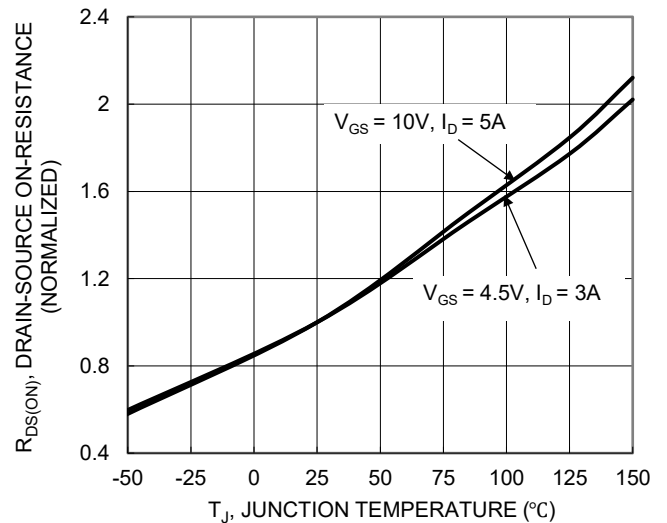


Figure 6. On-Resistance Variation with Temperature

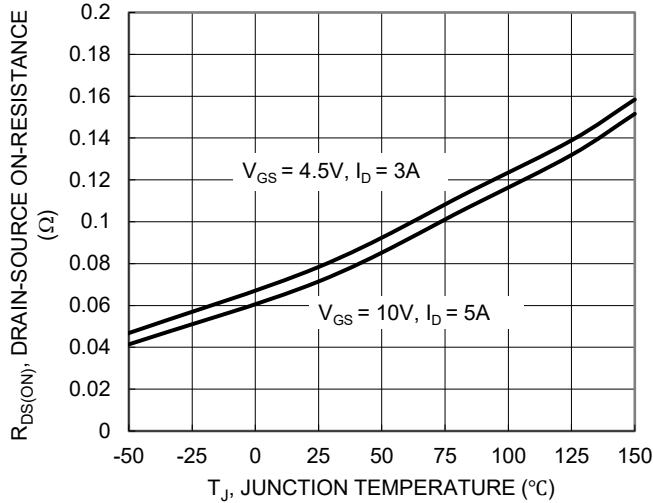


Figure 7. On-Resistance Variation with Temperature

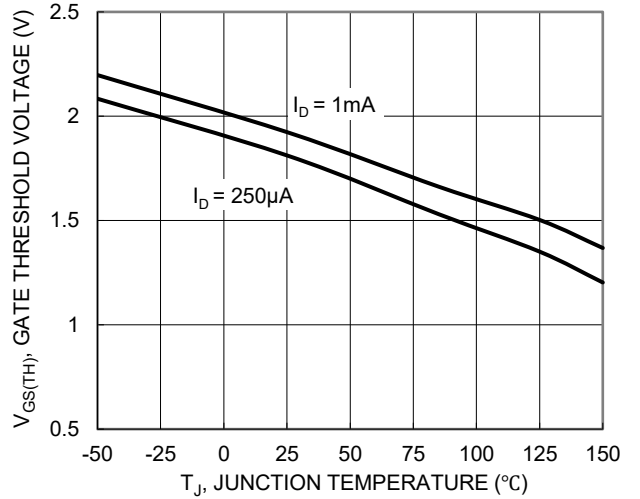


Figure 8. Gate Threshold Variation vs. Junction Temperature

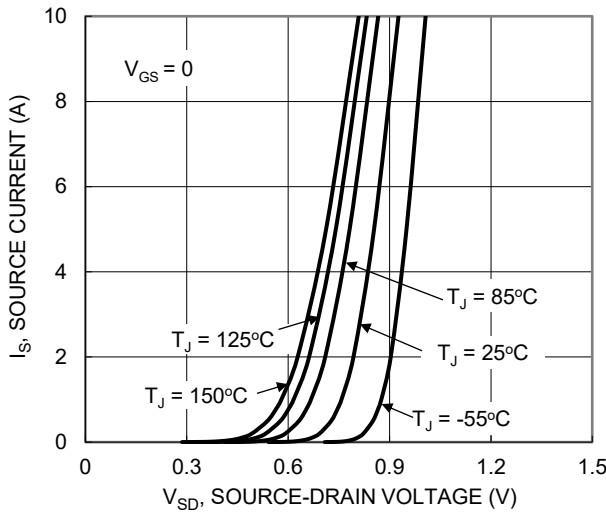


Figure 9. Diode Forward Voltage vs. Current

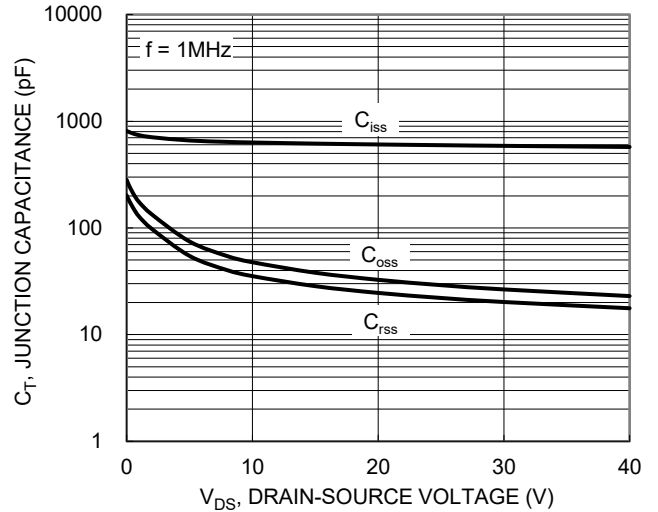


Figure 10. Typical Junction Capacitance

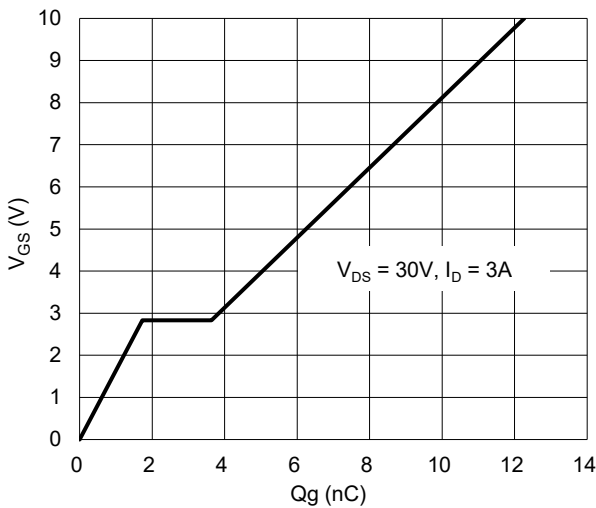


Figure 11. Gate Charge

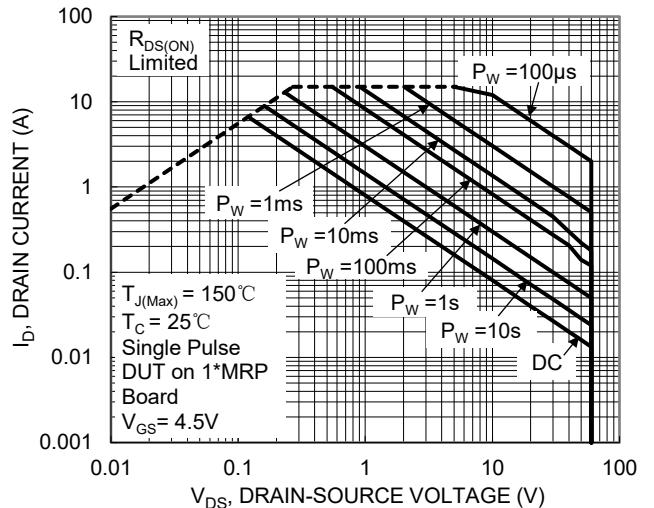


Figure 12. SOA, Safe Operation Area

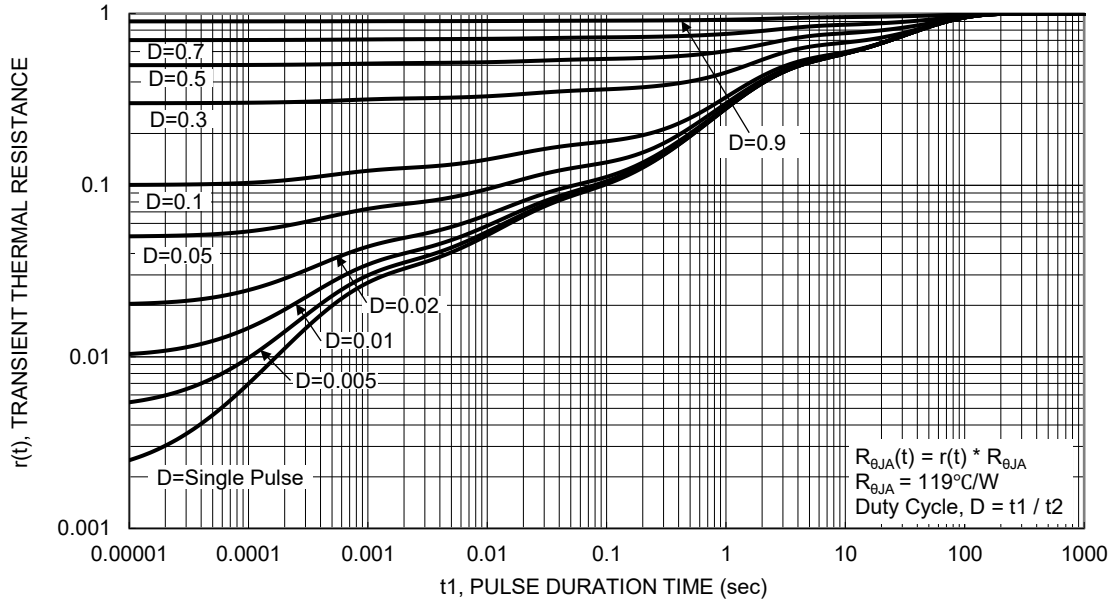
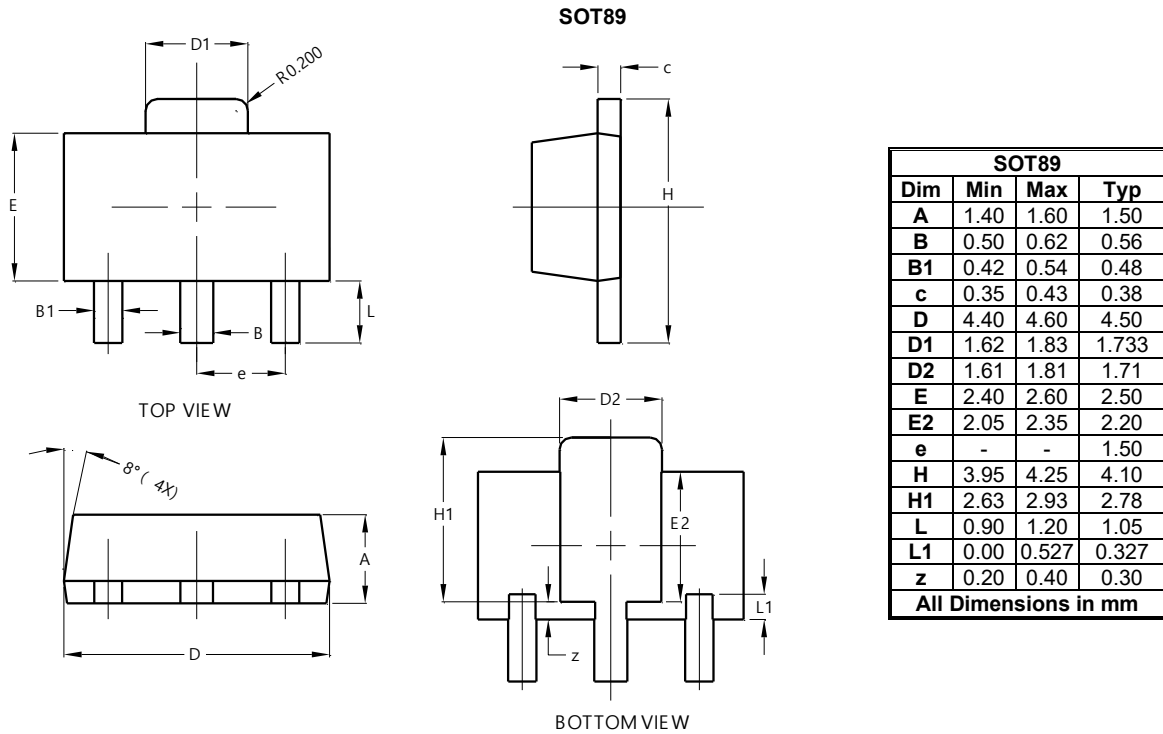


Figure 13. Transient Thermal Resistance

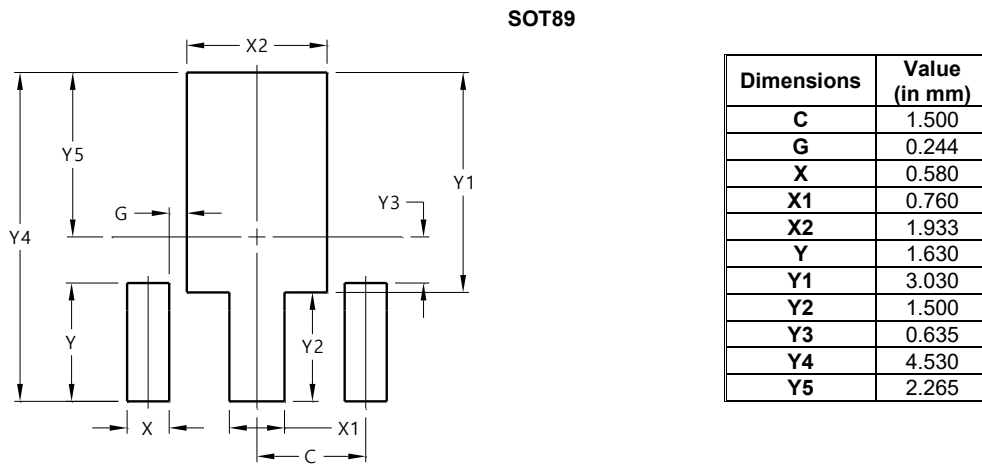
Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

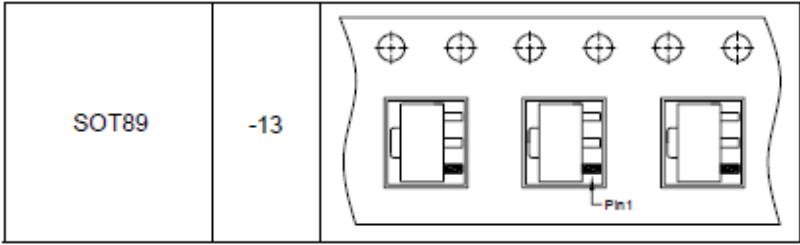


Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Device Tape Orientation (Notes 10 & 11)



- Notes: 10. For part marking, refer to product datasheet.
11. Tape and package drawings are not to scale and are shown for device tape orientation only.

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